



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-126C Plastic-Encapsulate Transistors

2SA1357 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 1.5 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -5 A

Collector-base voltage

$V_{(BR)CBO}$: -35 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-126C

1. EMITTER

2. COLLECTOR

3. BASE

1 2 3

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1mA, I_E=0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-8			V
Collector cut-off current	I_{CBO}	$V_{CB}=-35V, I_E=0$			-100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-8V, I_C=0$			-100	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2V, I_C=-0.5A$	100		320	
	$h_{FE(2)}$	$V_{CE}=-2V, I_C=-4A$	70			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-4A, I_B=-0.1A$			-1	V
Base-emitter voltage	V_{BE}	$V_{CE}=-2V, I_C=-4A$			-1.5	V
Transition frequency	f_T	$V_{CE}=-2V, I_C=-0.5A$		170		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		62		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320
Marking		

